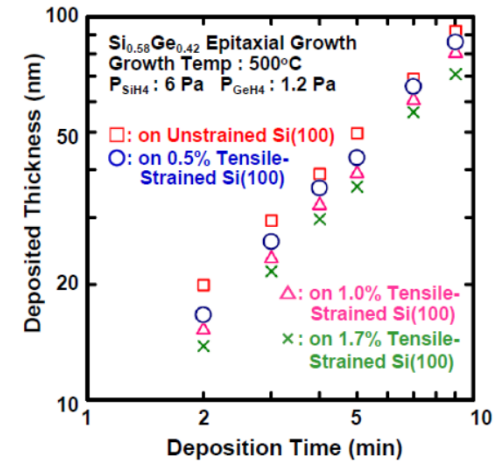
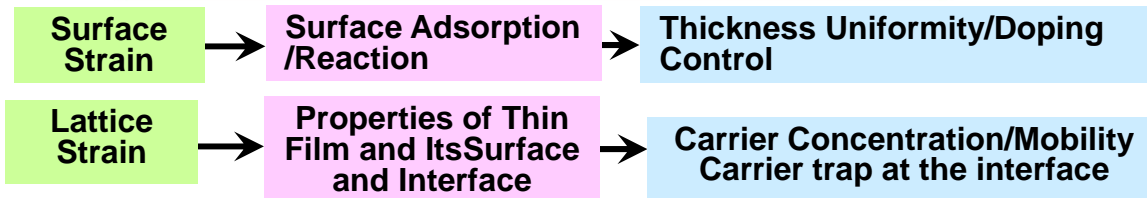
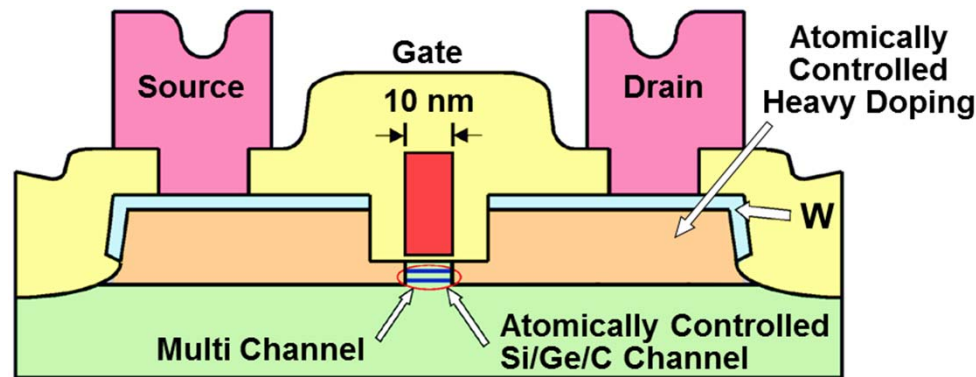
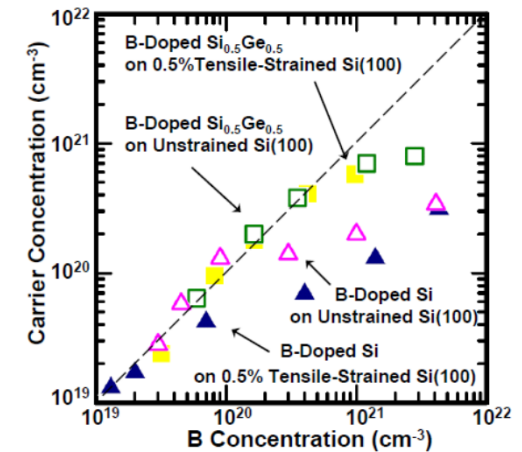
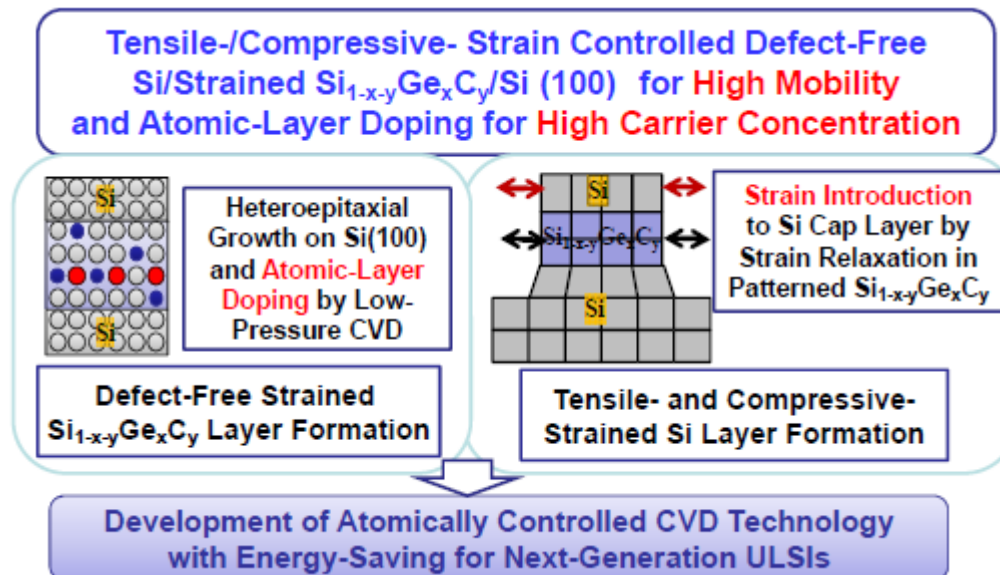


Atomically Controlled Processing of Si-Based Group IV Semiconductors for Energy Saving

Specially Appointed Professor Junichi Murota



Change of surface reaction by substrate surface strain.



Change of solid solubility for ionized impurity in Si-Ge film by strain